#### CS 222 Computer Organization & Architecture

Lecture 30 [12.04.2019]

#### **DRAM Organization**

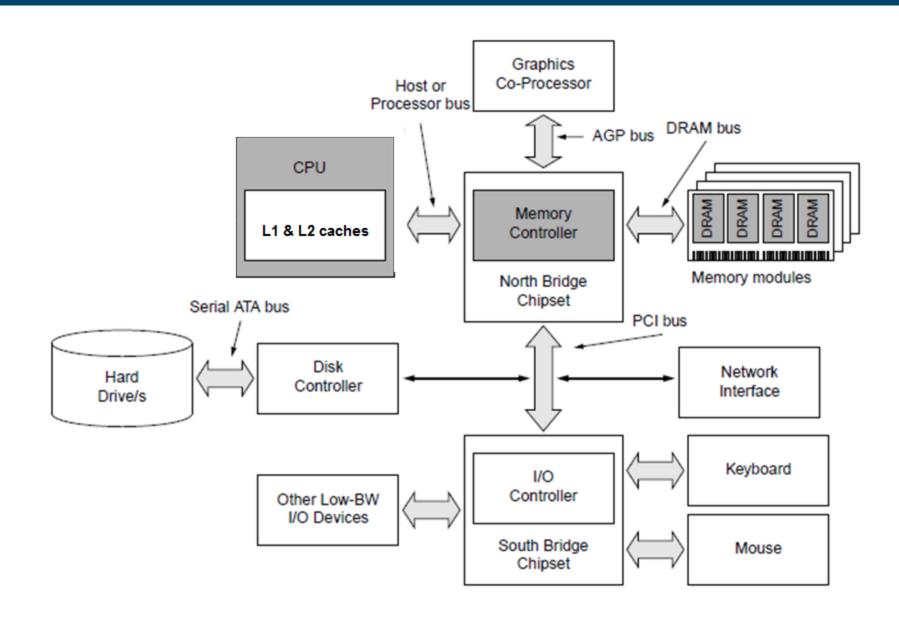


John Jose

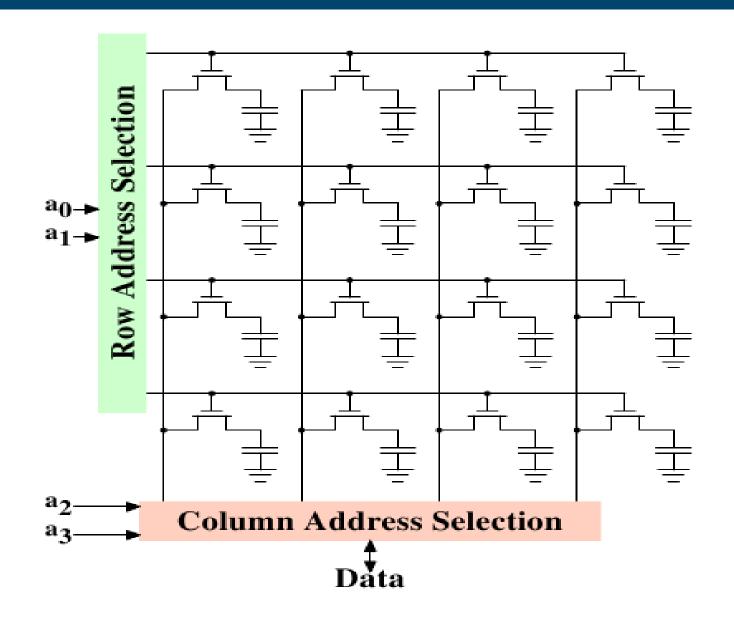
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### Components of a Modern Computer



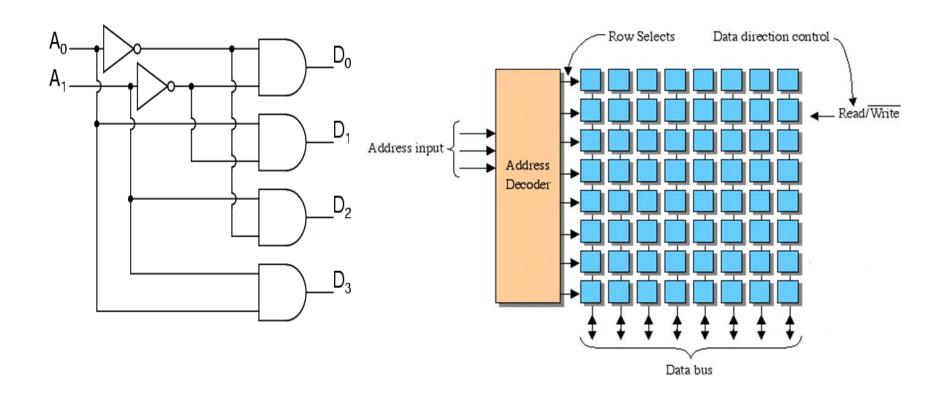
## DRAM (Dynamic Random Access Memory)



#### **Basic Terminologies**

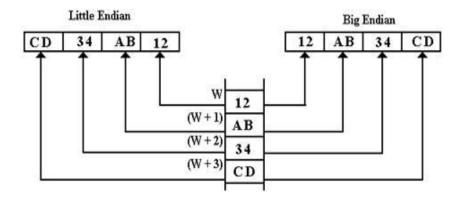
- Physical address space
  - Maximum size of main memory
  - Total number of uniquely identifiable locations
- Physical addressability
  - Minimum size of data in memory can be addressed
  - Byte-addressable, word-addressable, multibyte addressable
- Alignment
  - Does the hardware support unaligned access transparently to software?

# How memory works?

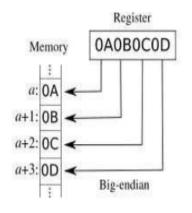


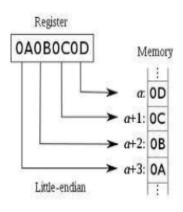
# **Byte Ordering**

#### ❖ Big Endian vs Little Endian



#### Big Endian vs. Little Endian





Int i = 
$$450 = 2^8 + 2^7 + 2^6 + 2 = x000001C2$$

LSB			e endia	
11000010	00000001	00000000	000000	00
C2	01	00	00	
lower	→ add	lress h	igher	
MSB			ig endia	
00000000	00000000	00000001	1100001	0
00	00	01	C2	

# Byte / Word Alignment



# Byte /Word Alignment

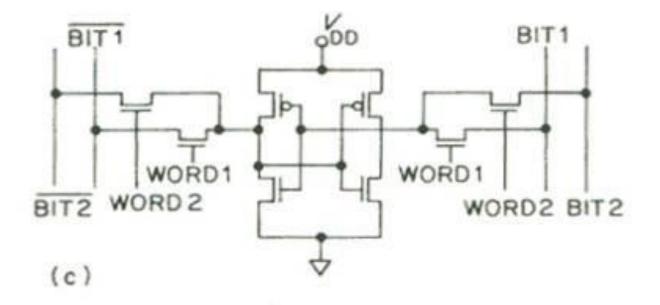
	Value of 3 low-order bits of byte address								
Width of object	0	1	2	3	4	5	6	7	
1 byte (byte)	Aligned	Aligned	Aligned	Aligned	Aligned	Aligned	Aligned	Aligned	
2 bytes (half word)	Alig	Aligned Aligned		Aligned		Aligned			
2 bytes (half word)		Misal	ligned	Misal	igned	Misaligned Misalign		Misaligned	
4 bytes (word)		Ali	Aligned Aligned						
4 bytes (word)			Misaligned Misaligned						
4 bytes (word)			Misaligned Misaligned					ligned	
4 bytes (word)			Misaligned Misaligne						
8 bytes (double word)	Aligned								
8 bytes (double word)	Misaligned								
8 bytes (double word)	Misaligned								
8 bytes (double word)	Misaligned								
8 bytes (double word)	Misaligned								
8 bytes (double word)			Misaligned						
8 bytes (double word)							Misa	ligned	
8 bytes (double word)								Misaligned	

#### **Enabling High Bandwidth Memories**

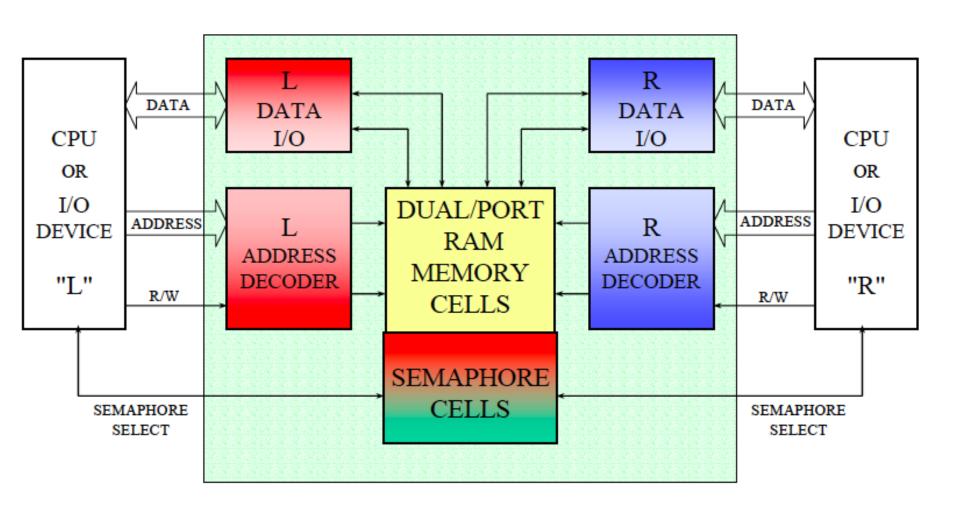
- Multiple Instructions per Cycle can generate multiple cache/memory accesses per cycle
- How do we ensure the cache/memory can handle multiple accesses in the same clock cycle?
- Solutions:
  - Multi-porting
  - Banking (interleaving)

## Multiporting

- Each memory cell has multiple read or write ports
- Truly concurrent accesses (no conflicts on reads)
- Expensive in terms of latency, power, area
- How read and write to the same location at same time?
  - Peripheral logic needs to handle this

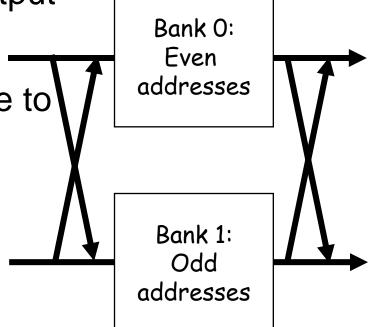


## **Peripheral Logic for Multiporting**



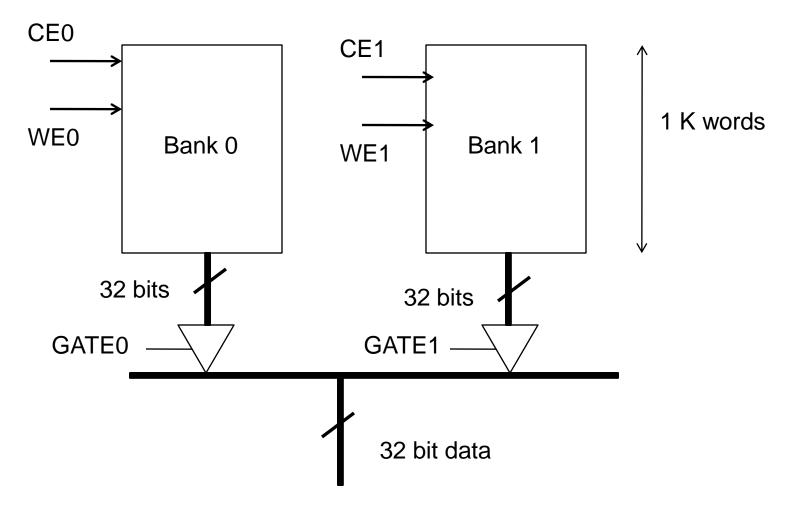
- Address space partitioned into separate banks
- ❖No increase in data store area
- Bits in address determines which bank an address maps
- Cannot satisfy multiple accesses to the same bank
- Crossbar interconnect in input/output

❖Bank conflicts - Two accesses are to the same bank difficult to handle

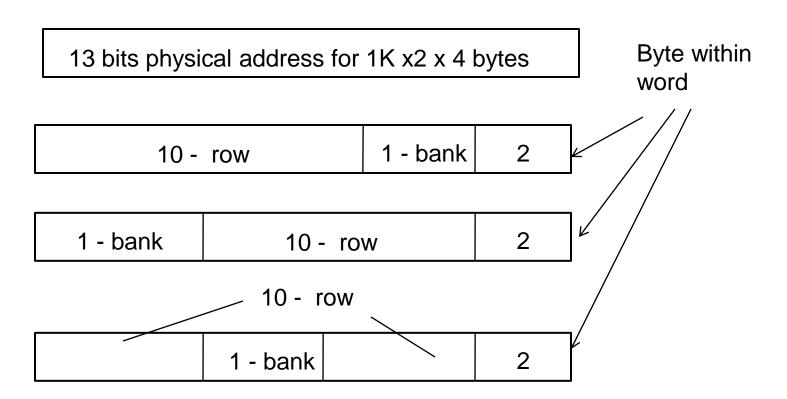


- Problem: a single monolithic memory array takes long to access and does not enable multiple accesses in parallel
- Goal: Reduce the latency of memory array access and enable multiple accesses in parallel
- Idea: Divide the entire memory into multiple banks that can be accessed independently (in the same cycle or in consecutive cycles)
- Accesses to different banks can be overlapped
- \*A Key Issue: How do you map data to different banks?

- Assume each bank supplies a word.
- Adjacent words are interleaved across banks



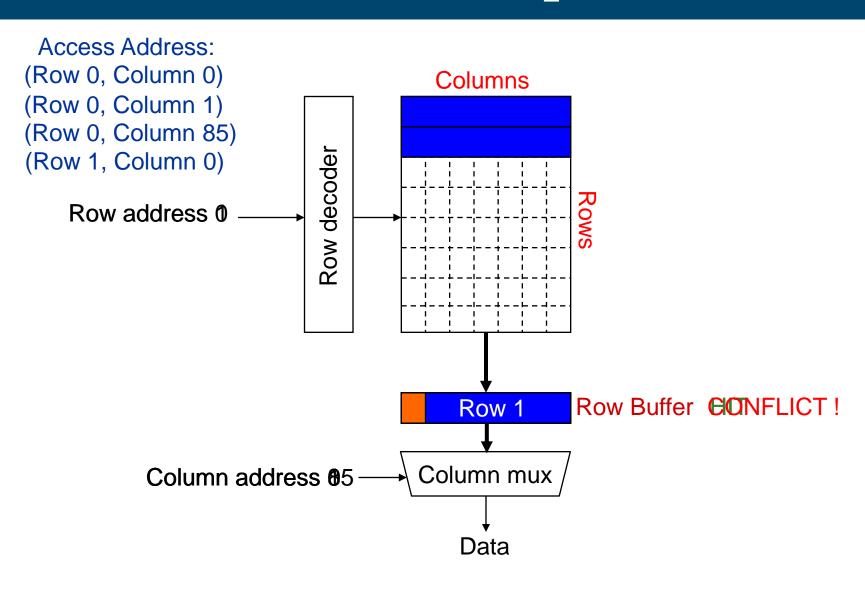
- Physical address split up for interleaving.
- Which bank do consecutive words in memory mapped to?



#### Page Mode DRAM

- ❖ A DRAM bank is a 2D array of cells: rows x columns
- ❖ A DRAM row is also called a DRAM page
- Sense amplifiers read values to the row buffer
- Each address is a <row,column> pair
- Access to a closed row
  - Activate (RAS) opens row (placed into row buffer)
  - \*Read/write (CAS)- access column in the row buffer
  - Precharge (PRE) closes the row and prepares the bank for next access
- \* Access to an open row
  - ❖No RAS only CAS needed

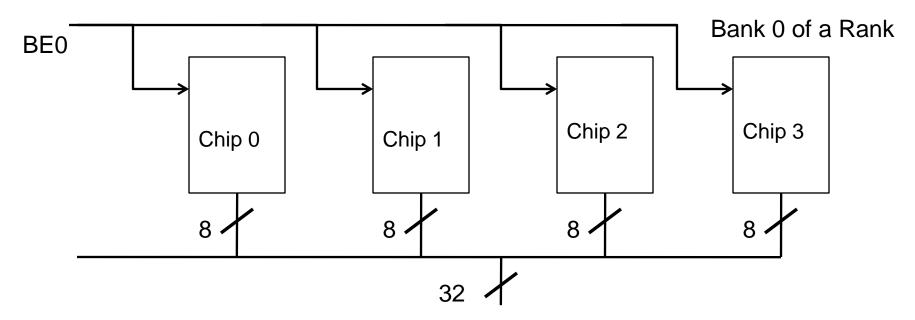
#### **DRAM Bank Operation**



## **DRAM Subsystem Organization**

- Channel
- **❖**DIMM
- **❖**Rank
- Chip
- **⇔**Bank
- \*Row
- Column
- **❖**B-Cell

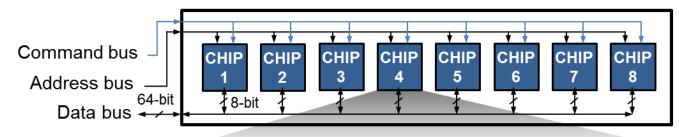
#### **DRAM Rank**



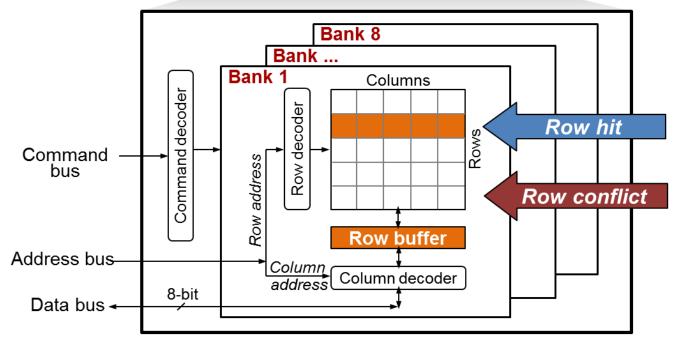
- Rank: A set of chips that respond to same command and same address at the same time but with different pieces of the requested data.
- Easy to produce 8 bit chip than 32 bit chip.
- Produce an 8 bit chip but control and operate them as a rank to get a 32 bit data in a single read.

#### **DRAM Rank**

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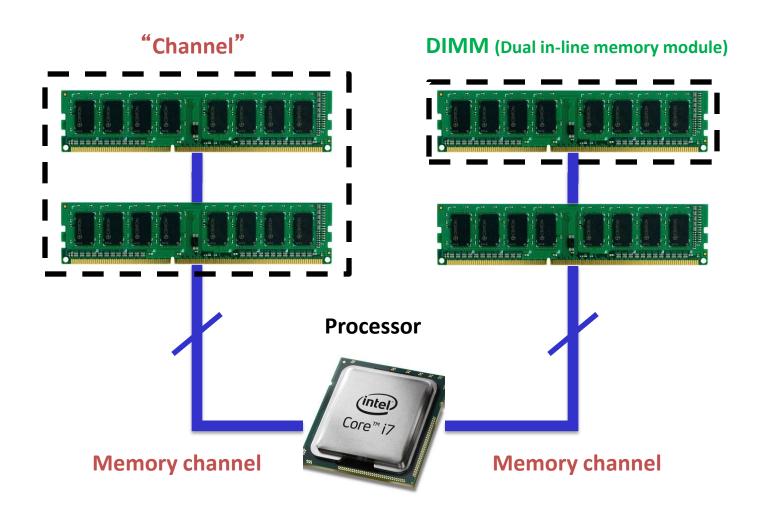


#### **DRAM Chip**

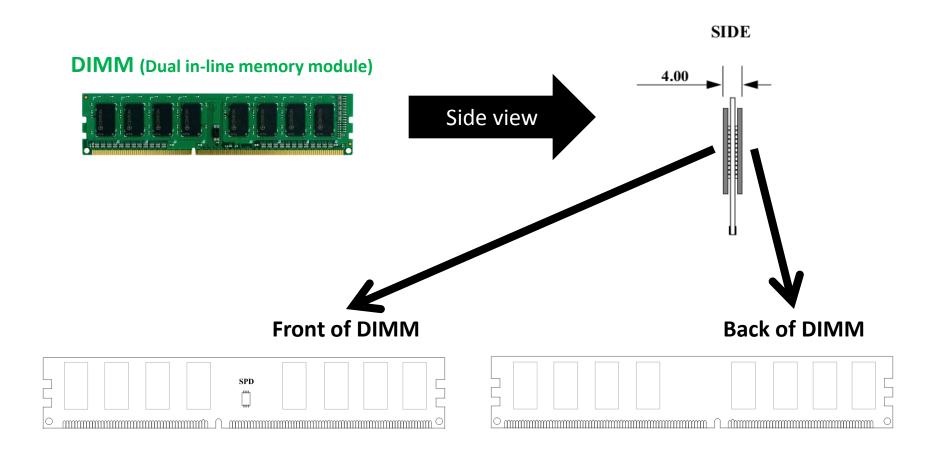


DRAM access latency varies depending on which row is stored in the row buffer

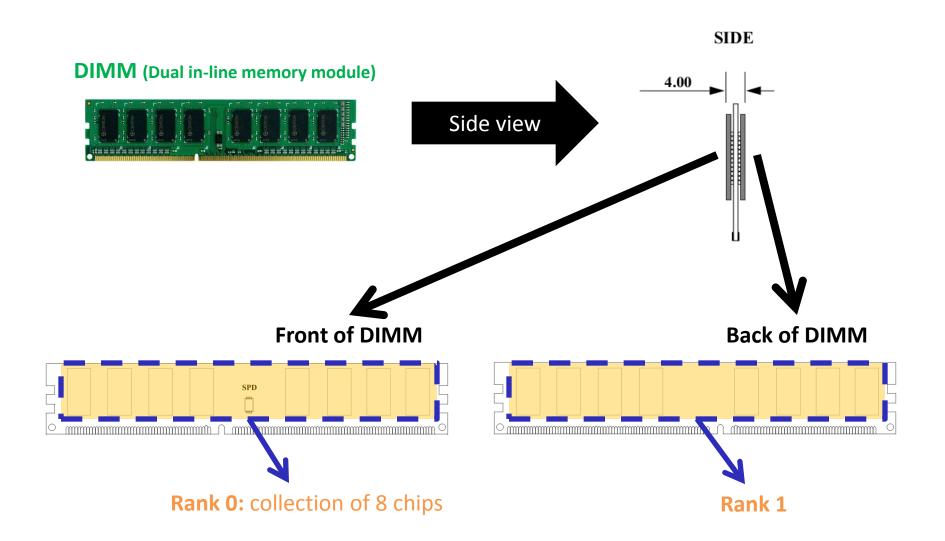
#### The DRAM subsystem



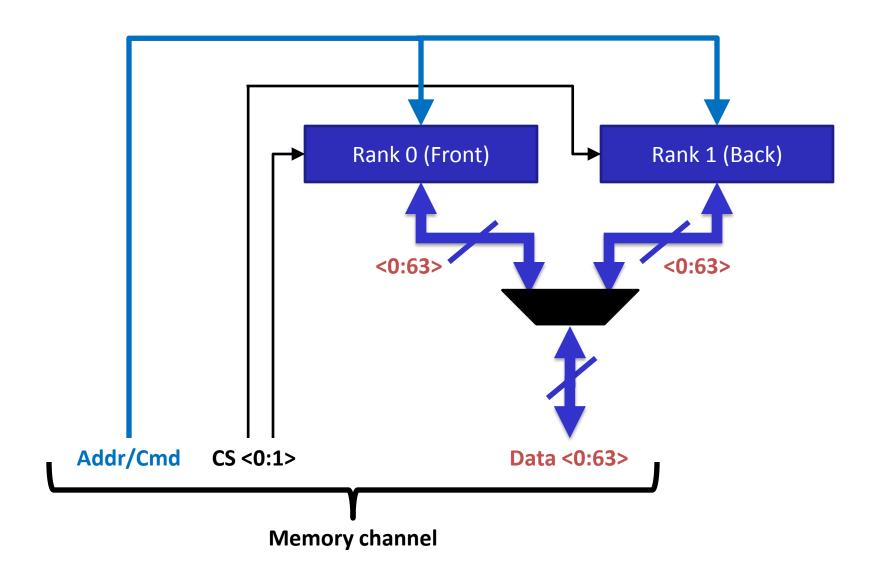
# Breaking down a DIMM



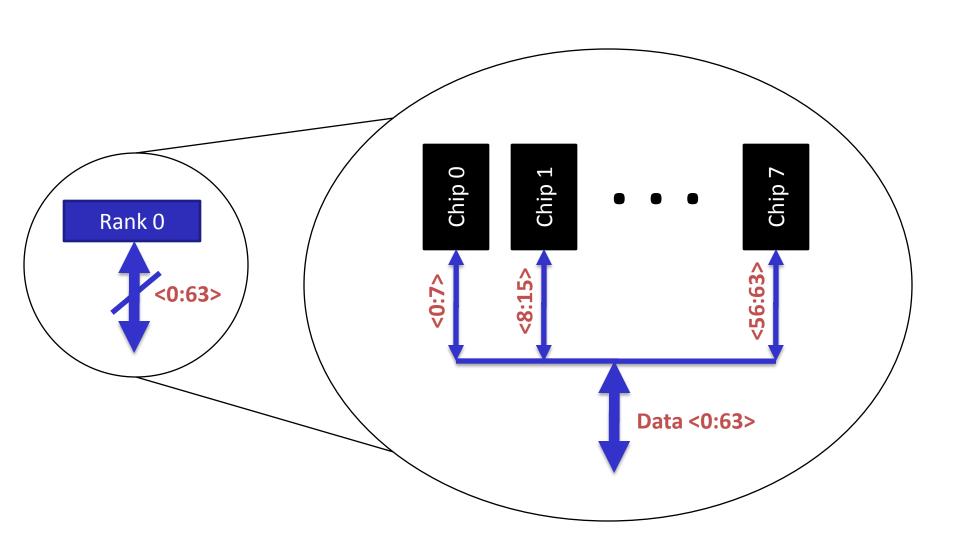
#### **Breaking down a DIMM**



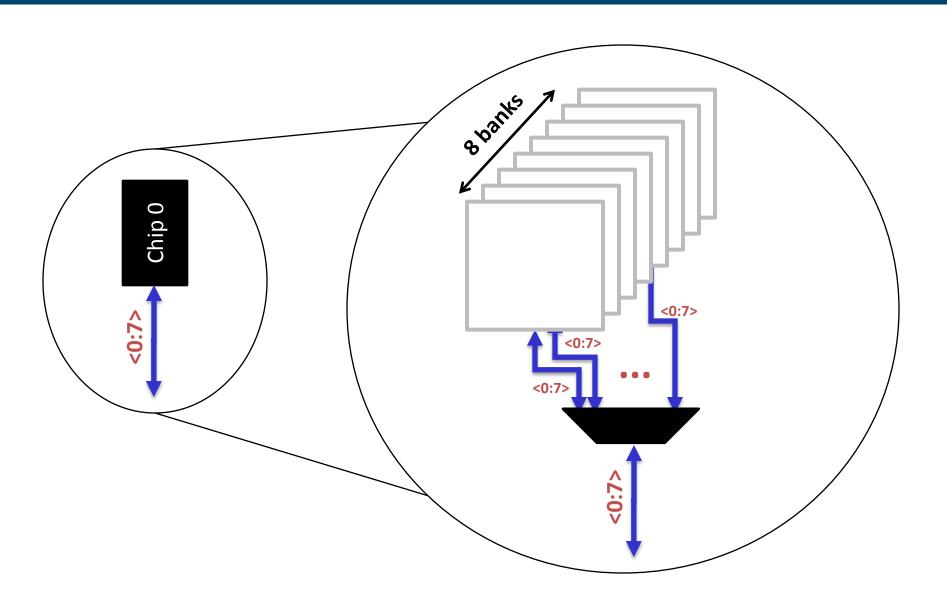
#### Rank



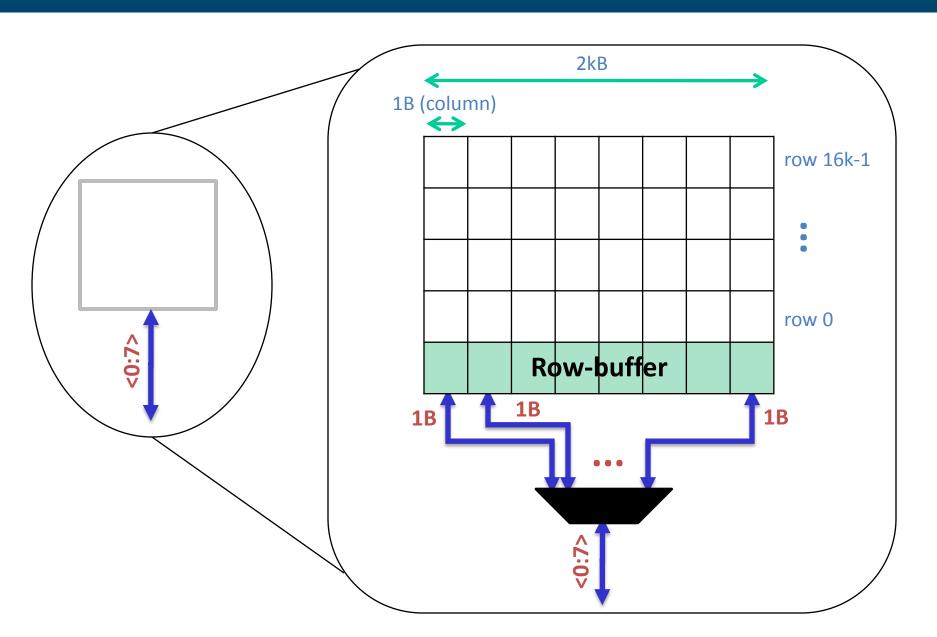
# Breaking down a Rank

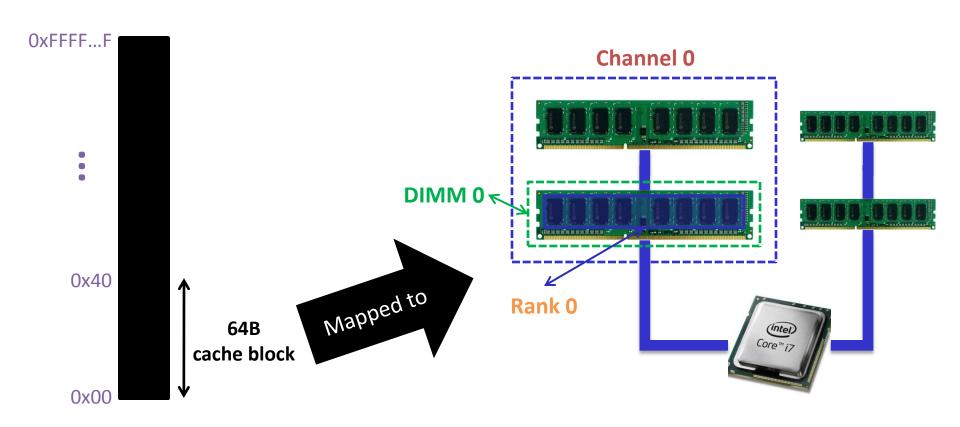


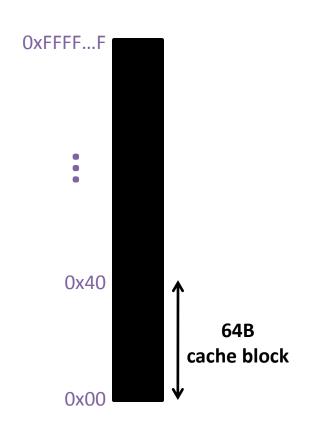
# Breaking down a Chip

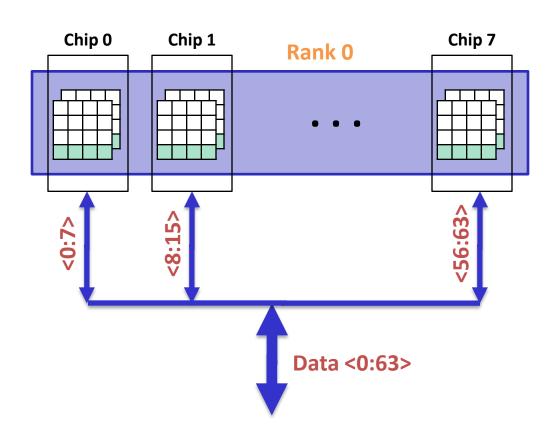


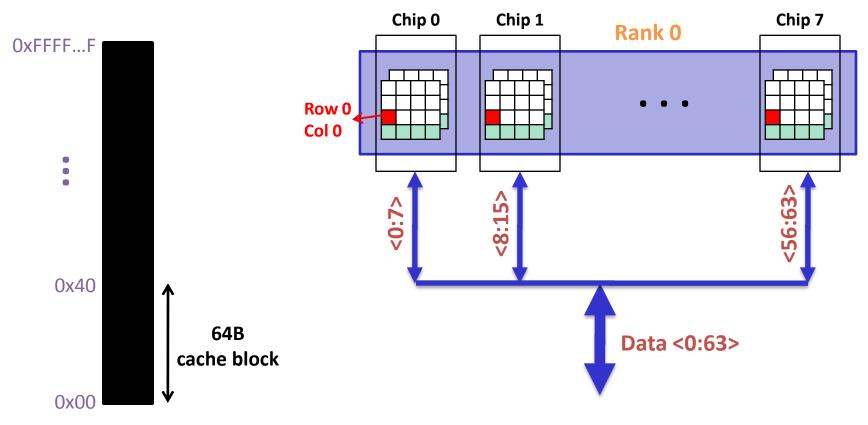
# Breaking down a Bank

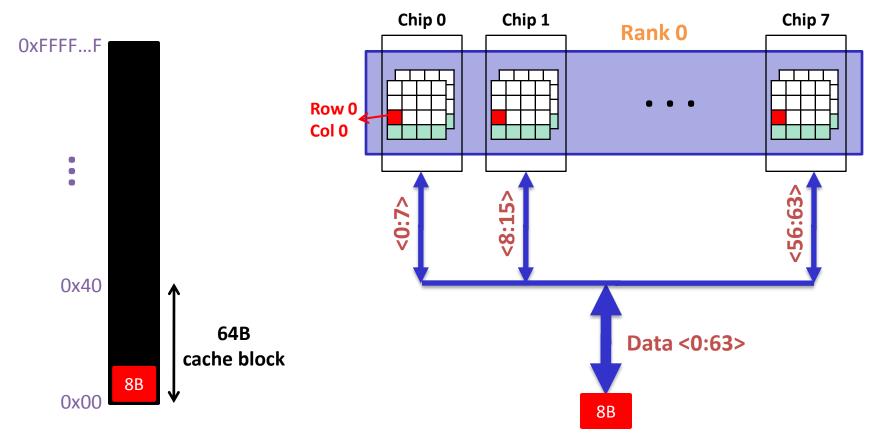


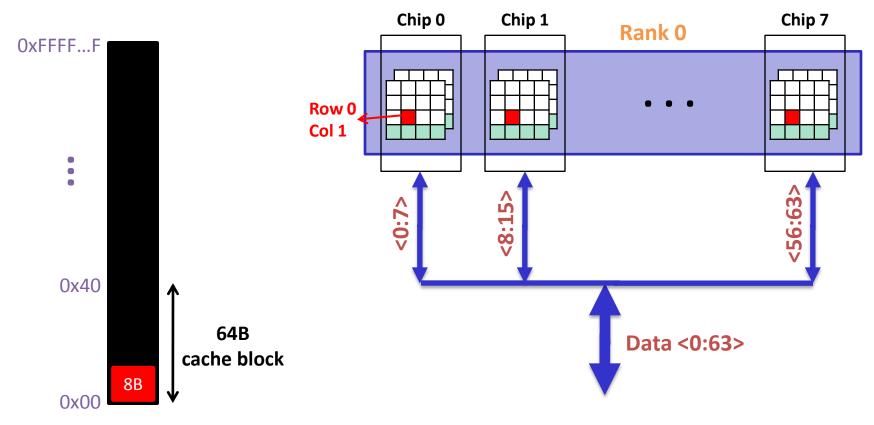


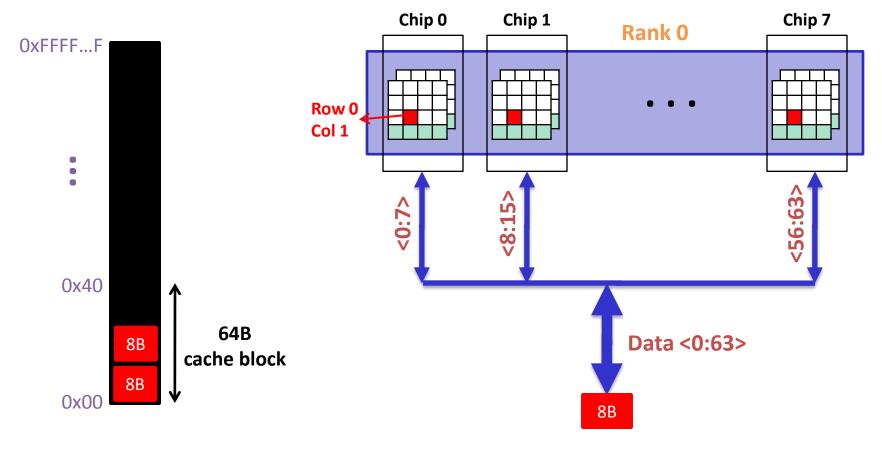












#### Physical memory space Chip 0 Chip 1 Chip 7 Rank 0 OxFFFF...F Row 0 Col 1 0x4064B Data < 0:63> 8B cache block 8B 0x00

A 64B cache block takes 8 I/O cycles to transfer. During the process, 8 columns are read sequentially.



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